## **Panasonic**

# **UP04878**

### Silicon N-channel MOSFET

#### For switching

#### ■ Features

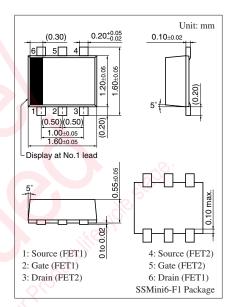
- Allowing 2.5 V drive
- Incorporating a built-in gate protection-diode
- Reduction of the mounting area and assembly cost by one half

#### ■ Basic Part Number

• 2SK3539 × 2

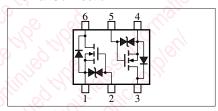
#### ■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	$V_{\mathrm{DSS}}$	50	V
Gate-source voltage (Drain open)	$V_{GSO}$	±7	V
Drain current	$I_{\mathrm{D}}$	100	mA
Peak drain current	$I_{DP}$	200	mA
Total power dissipation	P <sub>T</sub>	125	mW
Channel temperature	T <sub>ch</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55 to +125	°C



Marking Symbol: 7Y

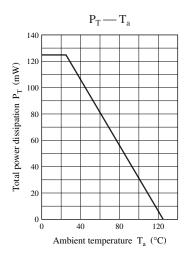
#### Internal Connection

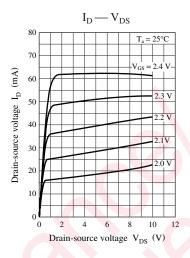


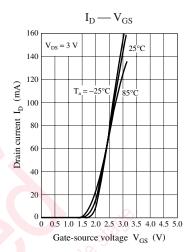
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

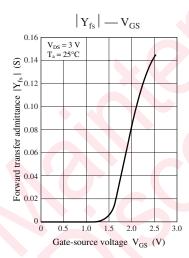
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V <sub>DSS</sub>	$I_D = 10 \mu\text{A},  V_{GS} = 0$	50			V
Drain-source cutoff current	$I_{DSS}$	$V_{DS} = 50 \text{ V}, V_{GS} = 0$			1.0	μΑ
Gate-source cutoff current	I <sub>GSS</sub>	$V_{GS} = \pm 7 \text{ V}, V_{DS} = 0$			±5	μΑ
Gate threshold voltage	V <sub>th</sub>	$I_D = 1 \mu A, V_{DS} = 3 V$	0.9	1.2	1.5	V
Drain-source ON resistance	R <sub>DS(on)</sub>	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$		8	15	Ω
		$I_D = 10 \text{ mA}, V_{GS} = 4.0 \text{ V}$		6	12	
Forward transfer admittance	Y <sub>fs</sub>	$I_D = 10 \text{ mA}, V_{GS} = 4.0 \text{ V}$	20	60		mS
Short-circuit forward transfer	C <sub>iss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		12		pF
capacitance (Common-source)						
Short-circuit output capacitance (Common-source)	C <sub>oss</sub>			7		pF
Reverse transfer capacitance	C <sub>rss</sub>			3		pF
(Common-source)						
Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, V_{GS} = 0 \text{ V to } 3 \text{ V}, R_{L} = 470 \Omega$		200		ns
Turn-off time	t <sub>off</sub>	$V_{DD} = 3 \text{ V}, V_{GS} = 3 \text{ V to } 0 \text{ V}, R_{L} = 470 \Omega$		200		ns

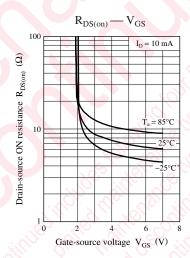
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.











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